

**Amendments to the Claims:**

The listing of claims will replace all prior version, and listings, of claims in the application.

**Listing of Claims**

**Claim 1 (Previously Presented)** A plasma apparatus capable of adaptive impedance matching, comprising:

a plasma reactor which produces plasma to proceed with chemical vapor deposition process;

a bi-polar electrostatic chuck which locates inside said plasma reactor to support and secure a wafer and said bi-polar electrostatic chuck has an inner electrode and an outer electrode;

an alternating current bias power which connects to said inner electrode and said outer electrode, and said alternating current bias power provides the bias for ion-bombardment on said wafer; and

an impedance matching circuit, said impedance matching circuit connects between said alternating bias power and said bi-polar electrostatic chuck in order to balance a power output of said inner electrode power and a power output of said outer electrode and said impedance matching circuit includes a plurality of adjustable impedance-elements, a power-measuring device, a power comparator, and an automatic impedance-regulator; the power outputs of said plurality of adjustable impedance-elements measured by said power-measuring device are compared by said power comparator to get a control signal and said control signal is sent to said automatic impedance-regulator in order to adjust impedance values of said plurality of adjustable impedance-elements.

**Claim 2 (Original)** The plasma apparatus capable of adaptive impedance matching according

to claim 1, wherein said plasma reactor has an alternating current plasma generating power.

**Claim 3 (Original)** The plasma apparatus capable of adaptive impedance matching according to claim 2, wherein the operating frequency of said alternating current plasma generating power is approximately between 200KHz and 350KHz.

**Claim 4 (Original)** The plasma apparatus capable of adaptive impedance matching according to claim 1, wherein the operating frequency of said alternating current bias power is about 13.56MHz.

**Claim 5 (Canceled)**

**Claim 6 (Previously Presented)** The plasma apparatus capable of adaptive impedance matching according to claim 1, wherein said power-measuring device has a voltage-meter for measuring amplitudes and phases of voltages and a current-meter for measuring amplitudes and phases of currents.

**Claim 7 (Previously Presented)** The plasma apparatus capable of adaptive impedance matching according to claim 1, wherein said power comparator has a transmitter for sending said control signal.

**Claim 8 (Previously Presented)** The plasma apparatus capable of adaptive impedance matching according to claim 1, wherein said automatic impedance-regulator has a receiver for receiving said control signal.

**Claim 9 (Previously Presented)** The plasma apparatus capable of adaptive impedance

matching according to claim 1, wherein said automatic impedance-regulator has a plurality of logic drive motors.

**Claims 10 – 14 (Canceled)**

**Claim 15 (Original)** High density plasma chemical vapor deposition equipment with an impedance-matching circuit, comprising:

an inductively-coupled plasma reactor which has an alternating current plasma generating power and said alternating current plasma generating power produces plasma to proceed with a high density plasma chemical vapor deposition process;

a bi-polar electrostatic chuck which locates inside said inductively-coupled plasma reactor to support and secure a wafer and said bi-polar electrostatic chuck has an inner electrode and an outer electrode, wherein said inner electrode locates inside the center portion of said bi-polar electrostatic chuck and said outer electrode locates inside the outer portion of said bi-polar electrostatic chuck outside said inner electrode;

a direct current power which connects to said bi-polar electrostatic chuck and said direct current power provides plus power to said inner electrode of said bi-polar electrostatic chuck and minus power to said outer electrode of said bi-polar electrostatic chuck;

an alternating current bias power which connects to said inner electrode and said outer electrode and said alternating current bias power provides the bias for ion-bombardment on said wafer;

an isolating circuit which connects between said direct current power and said alternating bias power, wherein said isolating circuit has a plurality of capacitors and a plurality of inductors, wherein said plurality of capacitors are used to prevent direct currents from flowing into said alternating current bias power and said plurality of

inductors are used to prevent alternating currents from flowing into said direct current power; and

an impedance matching circuit which includes a plurality of adjustable impedance-elements, a power-measuring device, a power comparator, and an automatic impedance-regulator, wherein power outputs of said plurality of adjustable impedance-elements measured by said power-measuring device are compared by said power comparator to get a control signal and said control signal is sent to said automatic impedance-regulator in order to adjust the impedance values of said plurality of adjustable impedance-elements.

**Claim 16 (Original)** The high density plasma chemical vapor deposition equipment with an impedance-matching circuit according to claim 15, wherein said power-measuring device has a voltage-meter for measuring amplitudes and phases of voltages and a current-meter for measuring amplitudes and phases of currents.

**Claim 17 (Original)** The high density plasma chemical vapor deposition equipment with an impedance-matching circuit according to claim 15, wherein said power comparator has a transmitter for sending said control signal.

**Claim 18 (Original)** The high density plasma chemical vapor deposition equipment with an impedance-matching circuit according to claim 15, wherein said automatic impedance-regulator has a receiver for receiving said control signal.

**Claim 19 (Original)** The high density plasma chemical vapor deposition equipment with an impedance-matching circuit according to claim 15, wherein said automatic impedance-regulator has a plurality of logic drive motors.

**Claims 20 - 21 (Canceled)**